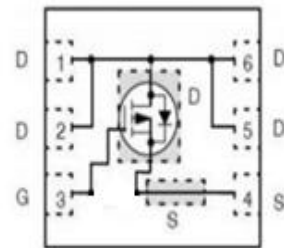
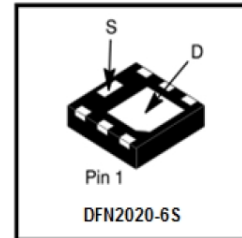


LP3418DT2AG

30V P-Channel (D-S) MOSFET

1. FEATURES

- VDS = -30V
 $R_{DS(ON)} \leq 25m\Omega$, VGS@-10V, IDS@-7.3A
 $R_{DS(ON)} \leq 38m\Omega$, VGS@-4.5V, IDS@-5.9A
- Low RDS(ON) trench technology.
- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. APPLICATIONS

- Load Switches
- DC/DC Conversion
- Motor Drives

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LP3418DT2AG	3B1	4000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	VDS	-30	V	
Gate-Source Voltage	VGS	± 20		
Continuous Drain Current(Note 1)	ID	-9.4	A	
Pulsed Drain Current(Note 2)	IDM	-40		
Maximum Power Dissipation(Note 1)	PD	TA = 25°C	3.1	W
		TA = 70°C	2	
Operating Junction and Storage Temperature Range	TJ , Tstg	-50~+150	°C	
Continuous Source Current (Diode Conduction)(Note 1)	IS	3.8	A	

Note: 1. Surface Mounted on 1" x 1" FR4 Board.

2. Pulse width limited by maximum junction temperature.

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit	
Maximum Junction-to-Ambient (Note 1)	RθJA	t ≤ 10S	40	°C/W
		Steady State	90	

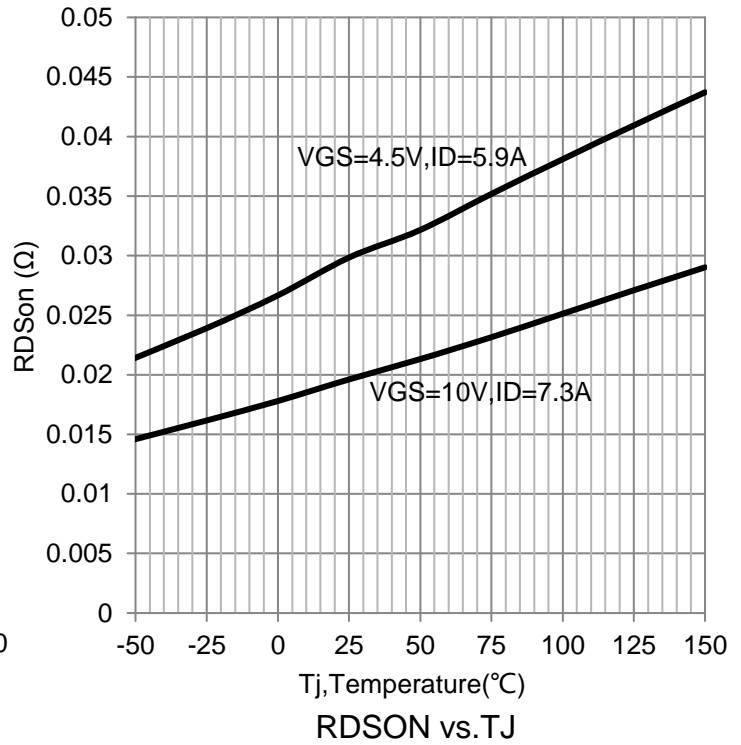
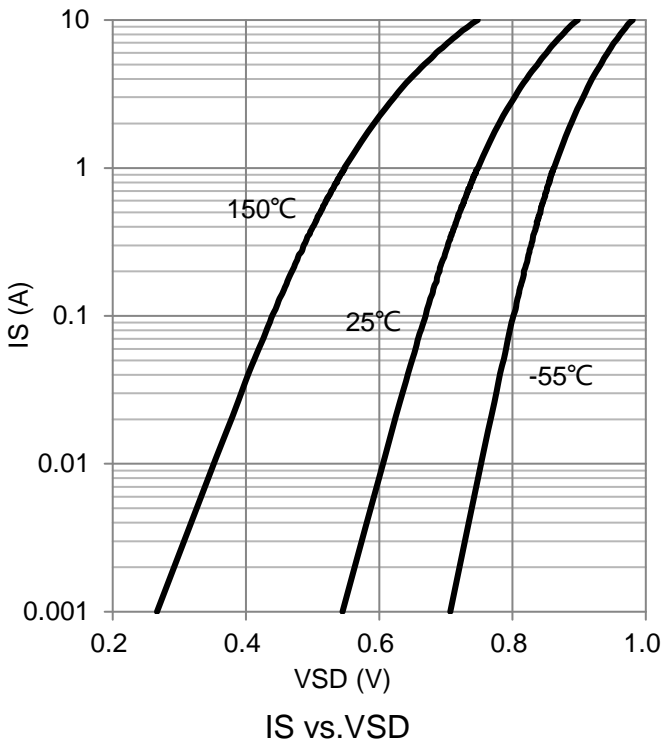
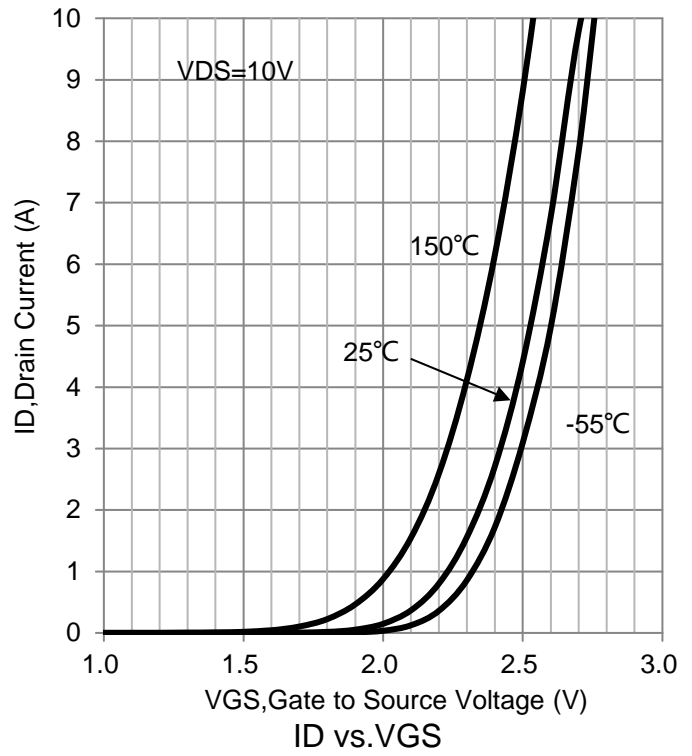
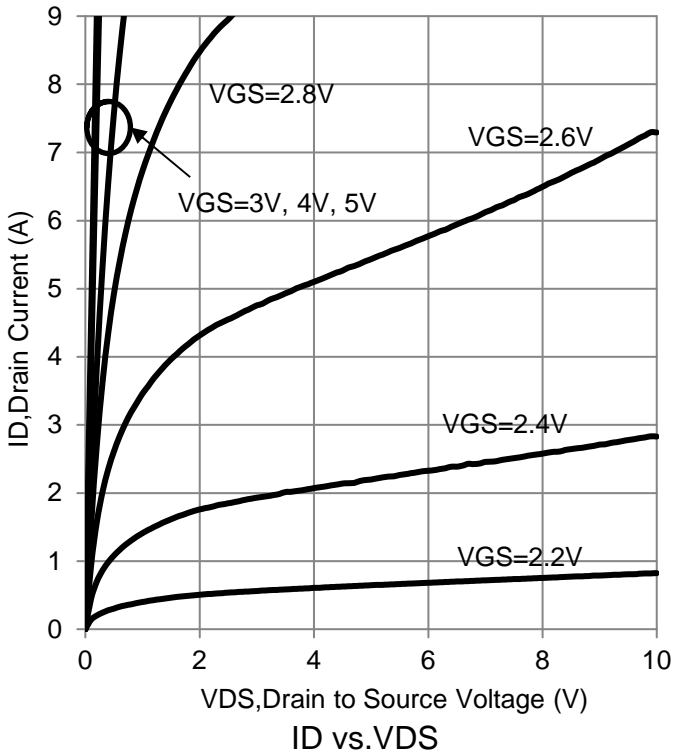
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS =0V, ID =-250μA)	V(BR)DSS	-30	-	-	V
Gate Threshold Voltage (VDS =VGS , ID =-250μA)	VGS(th)	-1	-	-3	V
Gate Leakage Current (VDS =0V, VGS =±20V)	IGSS	-	-	±100	nA
Zero Gate Voltage Drain Current (VDS =-24V, VGS =0V)	IDSS	-	-	-1	μA
On-State Drain Current(Note 3) (VDS = -5 V, VGS = -10 V)	ID(on)	-14	-	-	A
Drain-Source On-Resistance (VGS =-10V, ID = -7.3A)	RDS(ON) (Note 3)	-	-	25	mΩ
Drain-Source On-Resistance (VGS =-4.5V, ID = -5.9A)		-	-	38	
Diode Forward Voltage(Note 3) (IS =-1A, VGS =0V)	VSD	-	-	-1.5	V
Forward Transconductance(Note 3) (VDS = -15 V, ID = -7.3 A)	gfs	-	8	-	S
DYNAMIC(Note 4)					
Total Gate Charge	(VDS = -15 V, VGS = -4.5 V, ID = -7.3 A)	Qg	-	19	nC
Gate-Source Charge		Qgs	-	4.7	
Gate-Drain Charge		Qgd	-	8.4	
Input Capacitance	(VDS = -15 V, VGS = 0 V, f = 1 MHz)	Ciss	-	1539	pF
Output Capacitance		Coss	-	163	
Reverse Transfer Capacitance		Crss	-	151	
Turn-On Delay Time	(VDS = -15 V, RL =2.1 Ω, ID = -7.3 A, VGEN = -10 V, RGEN = 6 Ω)	td(on)	-	6	ns
Turn-On Rise Time		tr	-	5	
Turn-Off Delay Time		td(off)	-	55	
Turn-Off Fall Time		tf	-	21	

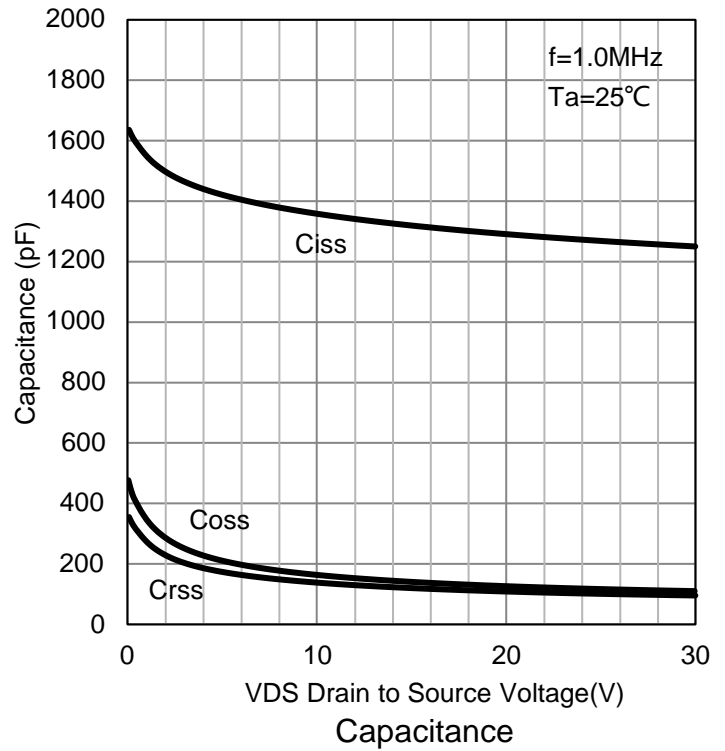
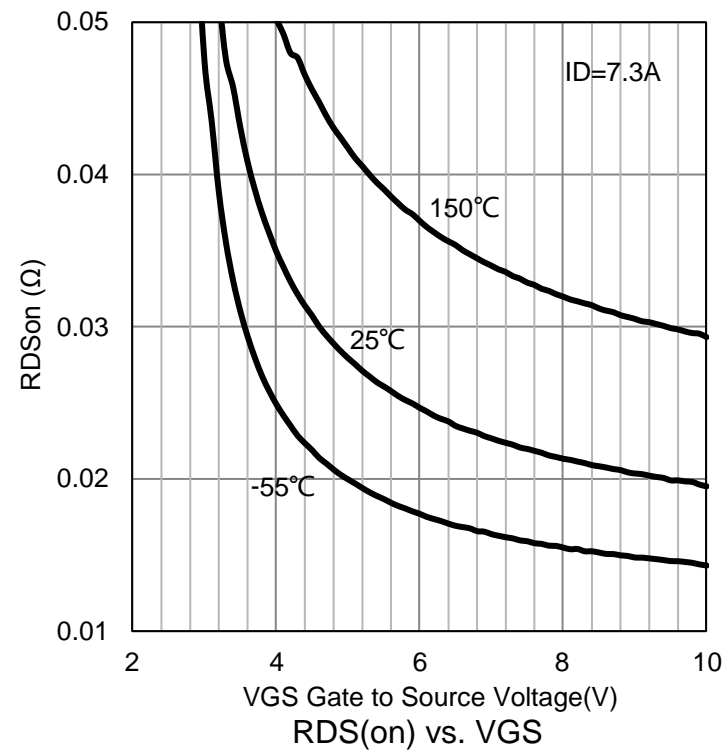
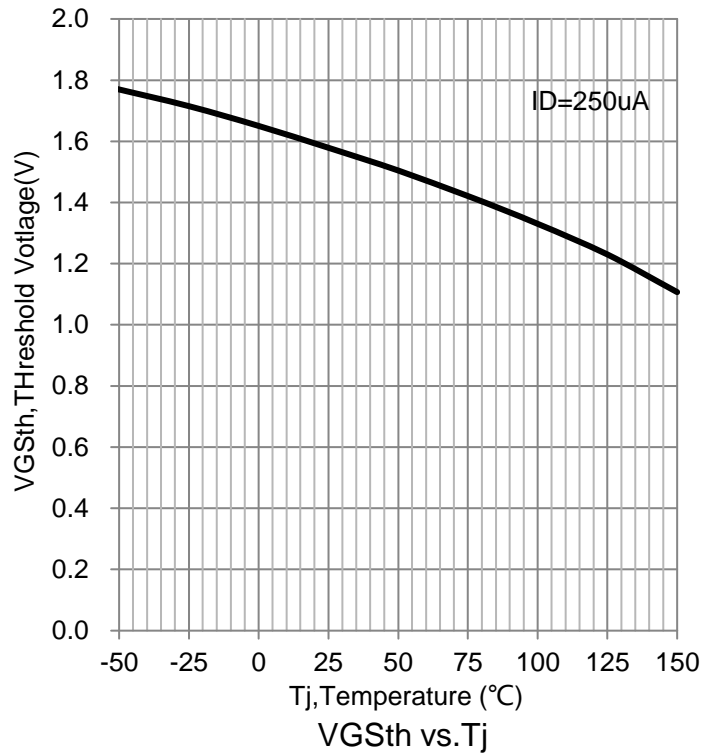
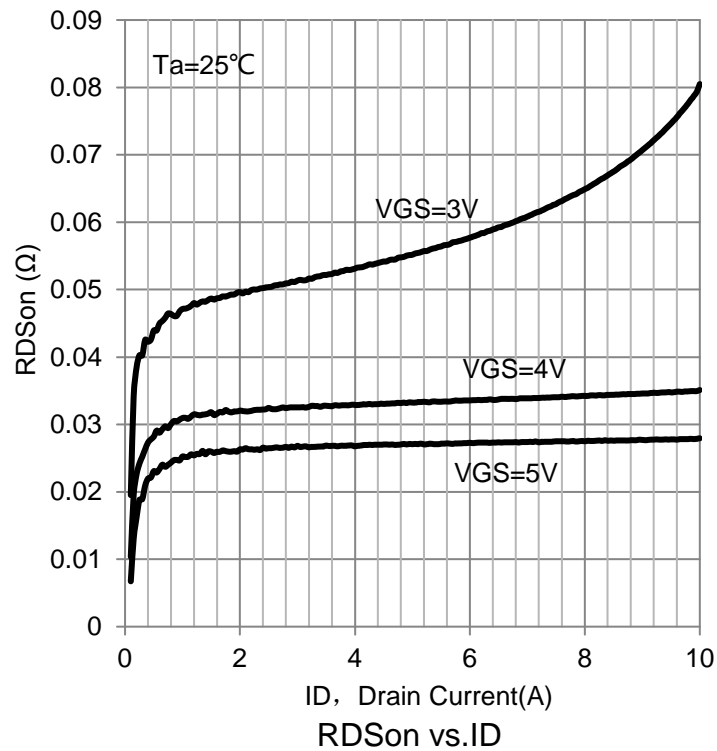
Note: 3. Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%.

4. Guaranteed by design, not subject to production testing.

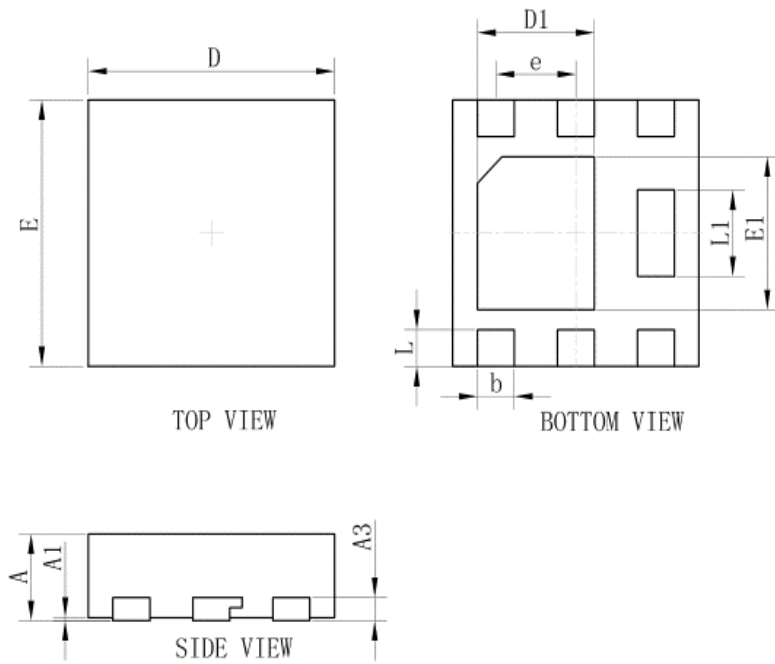
7. ELECTRICAL CHARACTERISTICS CURVES



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

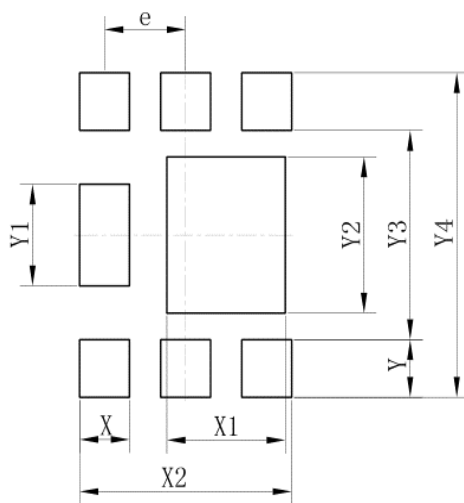


8. OUTLINE AND DIMENSIONS



DFN2020-6S			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.01	0.03	0.05
b	0.25	0.30	0.35
D	1.95	2.00	2.05
E	1.95	2.00	2.05
e	0.65TYP.		
L	0.23	0.28	0.33
L1	0.60	0.65	0.65
D1	0.90	0.95	1.00
E1	1.10	1.15	1.20
A3	0.152REF		
All Dimensions in mm			

9. SOLDERING FOOTPRINT



DFN2020-6S	
Dim	(mm)
X	0.40
X1	0.95
X2	1.70
e	0.65
Y	0.43
Y1	0.75
Y2	1.15
Y3	1.54
Y4	2.39

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)